Silicon NPN Power Transistors 2SC4106

DESCRIPTION

- With TO-220C package
- High breakdown voltage and high reliability
- Fast switching speed.
- Wide area of safe operation

APPLICATIONS

- 400V/7A switching regulator applications

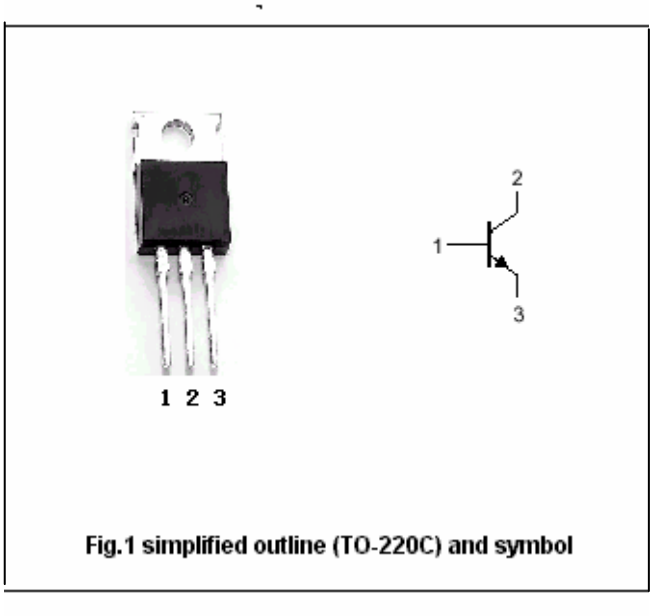

Fig.1 simplified outline (TO-220C) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		14	A
I_B	Base current		3	A
P_C	Collector dissipation	Ta=25℃	1.75	W
		T_C=25℃	50	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=5mA ; R_{BE}=∞	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ; I_E=0	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_B=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A; I_B=0.8A			0.8	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A; I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=400V ;I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			10	μA
h_{FE-1}	DC current gain	I_C=0.8A ; V_{CE}=5V	15		50	
h_{FE-2}	DC current gain	I_C=4A ; V_{CE}=5V	10			
h_{FE-3}	DC current gain	I_C=10mA ; V_{CE}=5V	10			
f_T	Transition frequency	I_C=0.8A ; V_{CE}=10V		20		MHz
C_{OB}	Collector output capacitance	f=1MHz ; V_{CB}=10V		80		pF
Switching times						
t_{on}	Turn-on time	I_C=5A;I_{B1}=1A; I_{B2}=-2A;R_L=40Ω V_{CC}=200V			0.5	μs
t_{stg}	Storage time				2.5	μs
t_f	Fall time				0.3	μs

◆ **h_{FE-1} classifications**

L	M	N
15-30	20-40	30-50

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PACKAGE OUTLINE

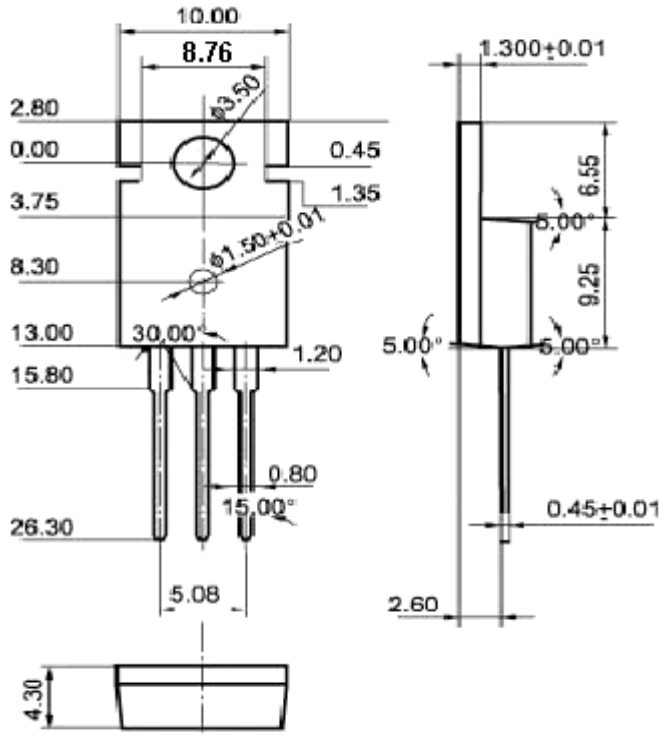

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

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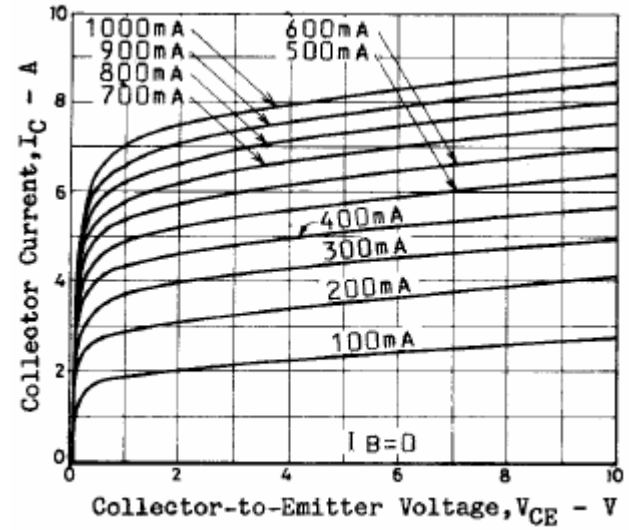

Fig.3 Static Characteristic

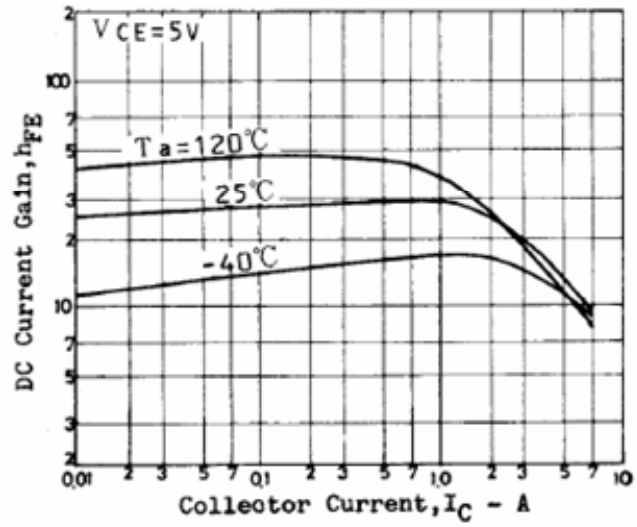

Fig.4 DC current Gain

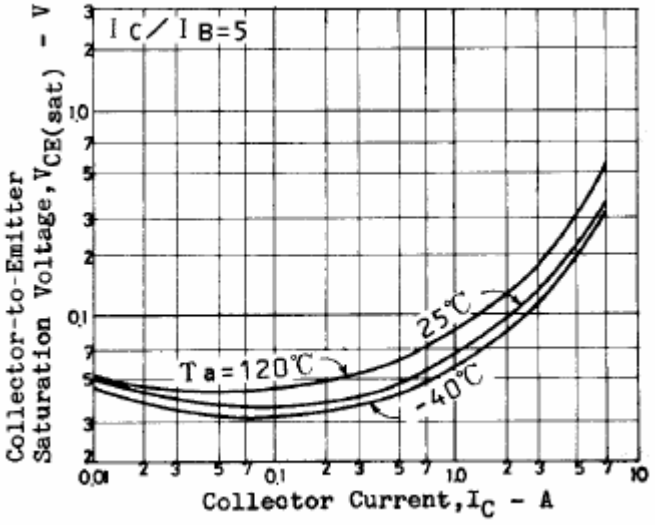

Fig.5 Collector-Emitter Saturation Voltage

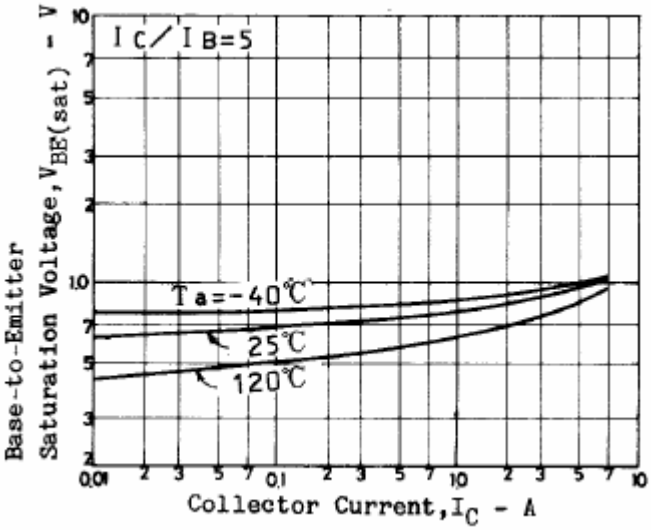

Fig.6 Base-Emitter Saturation Voltage

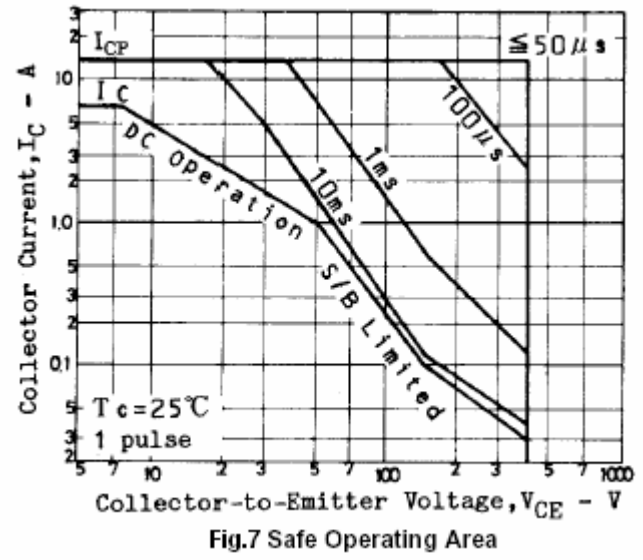

Fig.7 Safe Operating Area